

30022 U.S. Pat. App. No. 10032757
12/27/01
30022

N

PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10032757	FILING DATE 12/27/2001	CLASS 257	SUBCLASS 3	GAU 2811	EXAMINER
**APPLICANTS: Hui Angela; Fang Shengqing; Kinoshita Hiroyuki; Ko Kelwin; Li Wenmei; Sun Yu; Ogawa Hiroyuki; Chang Chi;					
**CONTINUING DATA VERIFIED:					
** FOREIGN APPLICATIONS VERIFIED:					
PG-PUB <input type="checkbox"/>		DO NOT PUBLISH <input checked="" type="checkbox"/>		RESCIND <input type="checkbox"/>	
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no 35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no Verified and Acknowledged Examiners's initials				ATTORNEY DOCKET NO G0728/2236P	
TITLE : Method and system for forming dual gate structures in a nonvolatile memory using a protective layer					
U.S. DEPT. OF COMM./PAT. & TM.-PTO-436L/Rev. 12-94					

NOTICE OF ALLOWANCE MAILED		Assistant Examiner		CLAIMS ALLOWED	
				Total Claims	Print Claim for O.G.
ISSUE FEE		Primary Examiner		DRAWING	
Amount Due	Date Paid			Sheets Drwg.	Figs. Drwg.
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE		Application Examiner	
WARNING: The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368, Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.					

FILED WITH:

☐ DISK (CRF)

☐ CD-ROM
(Attached in pocket on right inside flap)